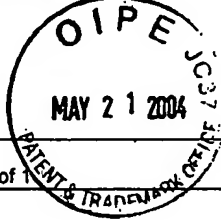


Substitute for form 1449A/PTO

INFORMATION DISCLOSURE STATEMENT BY APPLICANT

(Use as many sheets as necessary)



Complete if Known

Application Number	10/721585
Filing Date	November 25, 2003
First Named Inventor	Forbes, Leonard
Group Art Unit	2825
Examiner Name	Unknown C. Everhart

Sheet 1 of 1

Attorney Docket No: 1303.017US2

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1-7-05

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	Application Number	Unknown 10/721,585
	Filing Date	Even Date Herewith 11/25/03
	First Named Inventor	Forbes, Leonard
	Group Art Unit	Unknown 2625
	Examiner Name	Unknown C. Evenhart
Sheet 1 of 2		Attorney Docket No: 1303.017US2

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	Application Number	Unknown 10/721,585
	Filing Date	Even Date Herewith 11/25/03
	First Named Inventor	Forbes, Leonard
	Group Art Unit	Unknown 2826
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